

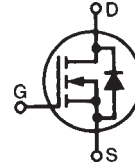
# X2-Class HiPerFET™ Power MOSFET

## IXFH34N60X2A

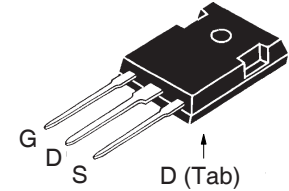
$$\begin{aligned} V_{DSS} &= 600V \\ I_{D25} &= 34A \\ R_{DS(on)} &\leq 100m\Omega \end{aligned}$$

AEC Q101 Qualified

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



TO-247



G = Gate      D = Drain  
S = Source    Tab = Drain

| Symbol     | Test Conditions                                                          | Maximum Ratings |                  |
|------------|--------------------------------------------------------------------------|-----------------|------------------|
| $V_{DSS}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                          | 600             | V                |
| $V_{DGR}$  | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 600             | V                |
| $V_{GSS}$  | Continuous                                                               | $\pm 30$        | V                |
| $V_{GSM}$  | Transient                                                                | $\pm 40$        | V                |
| $I_{D25}$  | $T_C = 25^\circ\text{C}$                                                 | 34              | A                |
| $I_{DM}$   | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 68              | A                |
| $I_A$      | $T_C = 25^\circ\text{C}$                                                 | 10              | A                |
| $E_{AS}$   | $T_C = 25^\circ\text{C}$                                                 | 1               | mJ               |
| $dv/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ | 50              | V/ns             |
| $P_D$      | $T_C = 25^\circ\text{C}$                                                 | 540             | W                |
| $T_J$      |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_{JM}$   |                                                                          | 150             | $^\circ\text{C}$ |
| $T_{stg}$  |                                                                          | -55 ... +150    | $^\circ\text{C}$ |
| $T_L$      | Maximum Lead Temperature for Soldering                                   | 300             | $^\circ\text{C}$ |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s                                      | 260             | $^\circ\text{C}$ |
| $M_d$      | Mounting Torque                                                          | 1.13 / 10       | Nm/lb.in         |
| Weight     |                                                                          | 6               | g                |

### Features

- International Standard Package
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified) | Characteristic Values |      |                       |
|--------------|-----------------------------------------------------------------------------|-----------------------|------|-----------------------|
|              |                                                                             | Min.                  | Typ. | Max.                  |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 1mA$                                                 | 600                   |      | V                     |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 2.5mA$                                           | 3.5                   |      | 5.0 V                 |
| $I_{GSS}$    | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$                                          |                       |      | $\pm 100$ nA          |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ\text{C}$             |                       |      | 10 $\mu A$<br>1.75 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                         |                       |      | 100 m $\Omega$        |

| Symbol                              | Test Conditions<br>( $T_J = 25^{\circ}\text{C}$ , Unless Otherwise Specified)                                                                       | Characteristic Values                                |      |                           |
|-------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------|------|---------------------------|
|                                     |                                                                                                                                                     | Min.                                                 | Typ. | Max                       |
| $g_{fs}$                            | $V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                                                                                          | 12                                                   | 20   | S                         |
| $R_{Gi}$                            | Gate Input Resistance                                                                                                                               |                                                      | 0.8  | $\Omega$                  |
| $C_{iss}$                           | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$                                                                                    |                                                      | 3230 | pF                        |
| $C_{oss}$                           |                                                                                                                                                     |                                                      | 2000 | pF                        |
| $C_{rss}$                           |                                                                                                                                                     |                                                      | 2    | pF                        |
| <b>Effective Output Capacitance</b> |                                                                                                                                                     |                                                      |      |                           |
| $C_{o(er)}$                         | Energy related                                                                                                                                      | $V_{GS} = 0\text{V}$<br>$V_{DS} = 0.8 \cdot V_{DSS}$ | 130  | pF                        |
| $C_{o(tr)}$                         | Time related                                                                                                                                        |                                                      | 486  | pF                        |
| $t_{d(on)}$                         | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 10\Omega$ (External) |                                                      | 37   | ns                        |
| $t_r$                               |                                                                                                                                                     |                                                      | 60   | ns                        |
| $t_{d(off)}$                        |                                                                                                                                                     |                                                      | 64   | ns                        |
| $t_f$                               |                                                                                                                                                     |                                                      | 30   | ns                        |
| $Q_{g(on)}$                         | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                                                                    |                                                      | 56   | nC                        |
| $Q_{gs}$                            |                                                                                                                                                     |                                                      | 19   | nC                        |
| $Q_{gd}$                            |                                                                                                                                                     |                                                      | 18   | nC                        |
| $R_{thJC}$                          |                                                                                                                                                     |                                                      |      | 0.23 $^{\circ}\text{C/W}$ |
| $R_{thCS}$                          | TO-220                                                                                                                                              |                                                      | 0.50 | $^{\circ}\text{C/W}$      |
|                                     | TO-247                                                                                                                                              |                                                      | 0.25 | $^{\circ}\text{C/W}$      |

## Source-Drain Diode

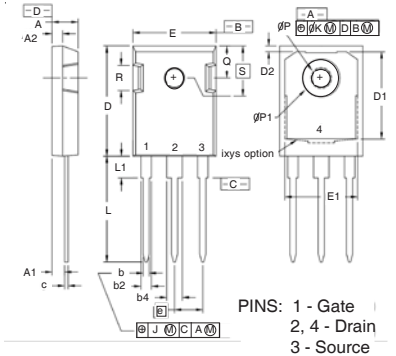
| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)    | Characteristic Values |      |               |
|----------|--------------------------------------------------------------------------------|-----------------------|------|---------------|
|          |                                                                                | Min.                  | Typ. | Max           |
| $I_S$    | $V_{GS} = 0\text{V}$                                                           |                       |      | 34 A          |
| $I_{SM}$ | Repetitive, pulse Width Limited by $T_{JM}$                                    |                       |      | 136 A         |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                    |                       |      | 1.4 V         |
| $t_{rr}$ | $I_F = 17\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ |                       | 164  | ns            |
| $Q_{RM}$ |                                                                                |                       | 1.2  | $\mu\text{C}$ |
| $I_{RM}$ |                                                                                |                       | 14.4 | A             |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

## ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

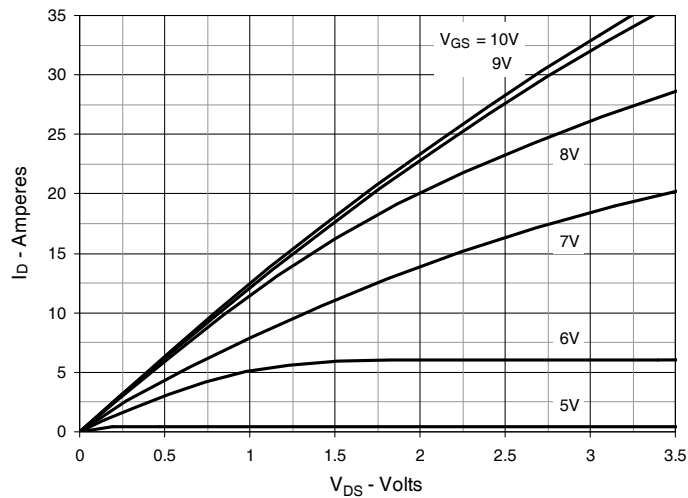
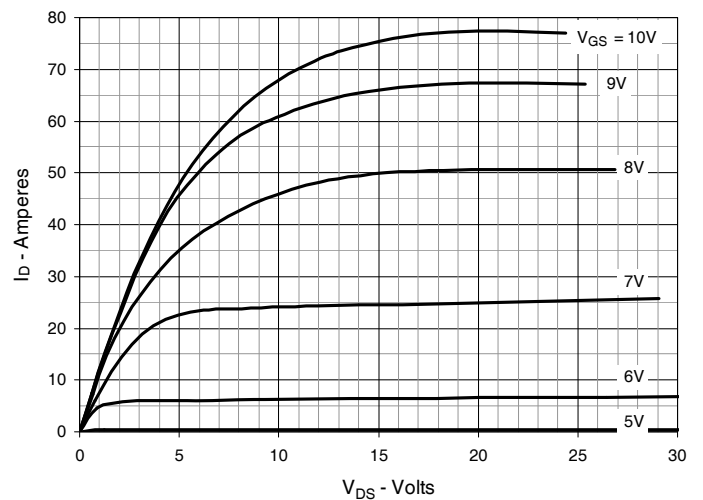
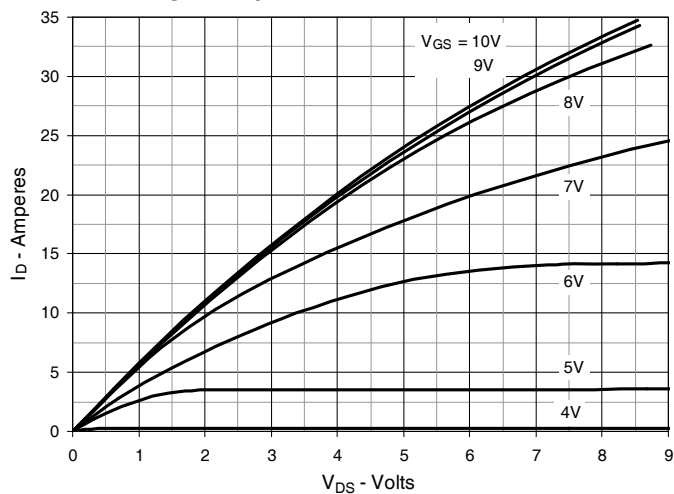
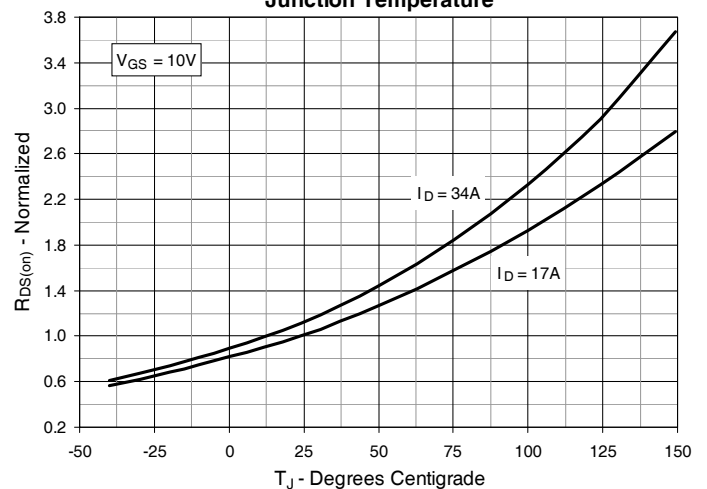
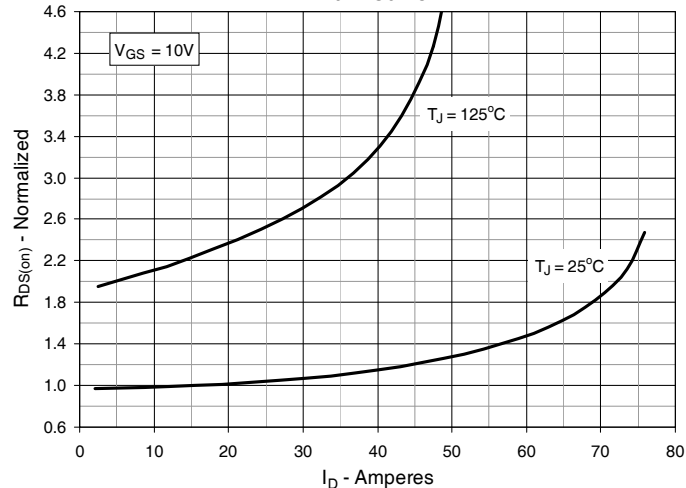
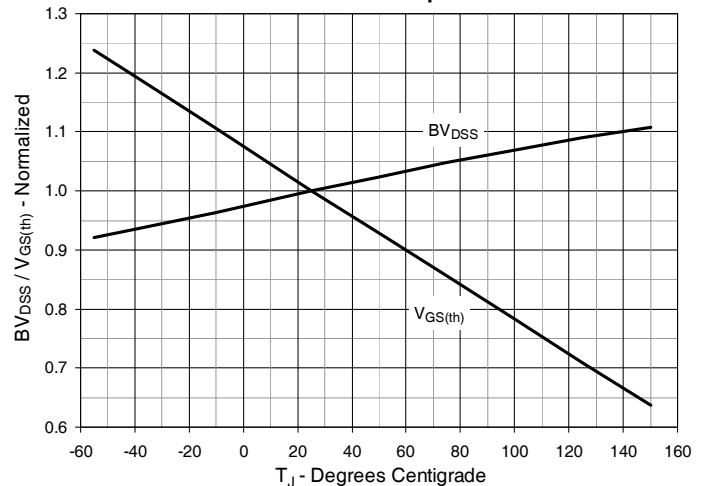
## TO-247 (IXFH) Outline

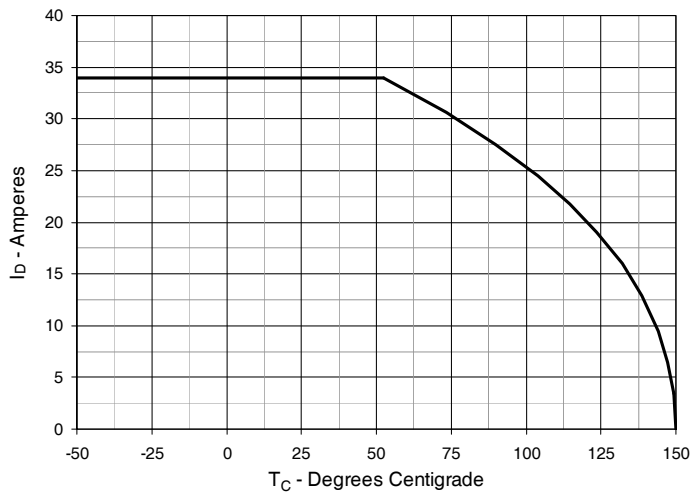
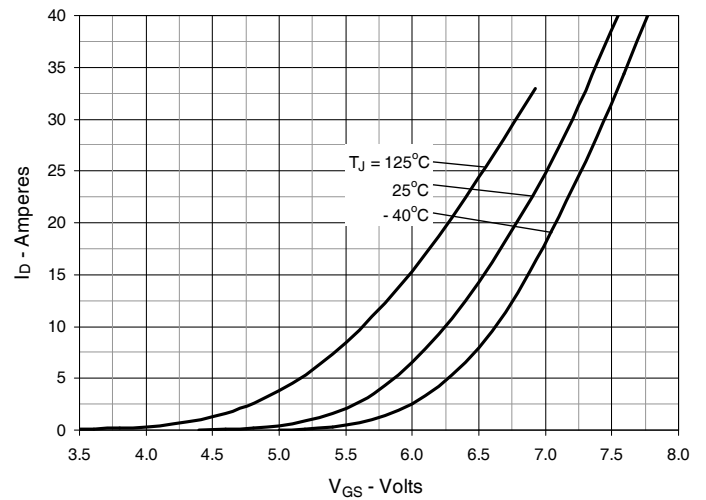
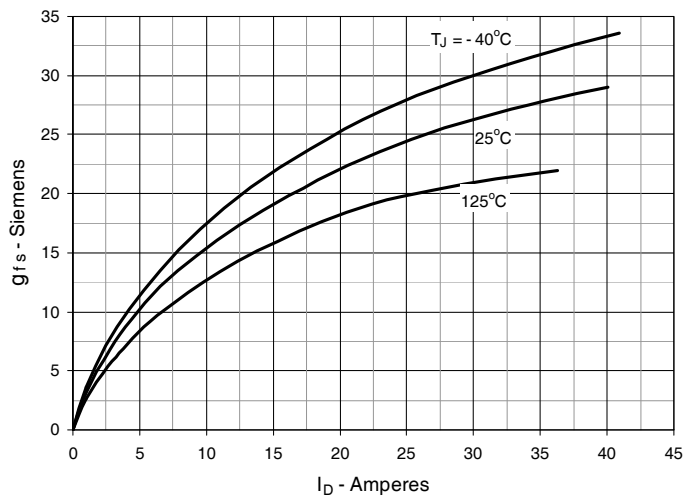
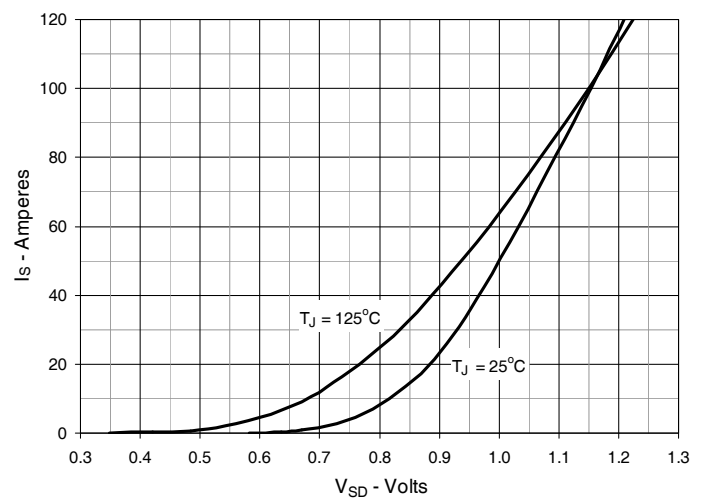
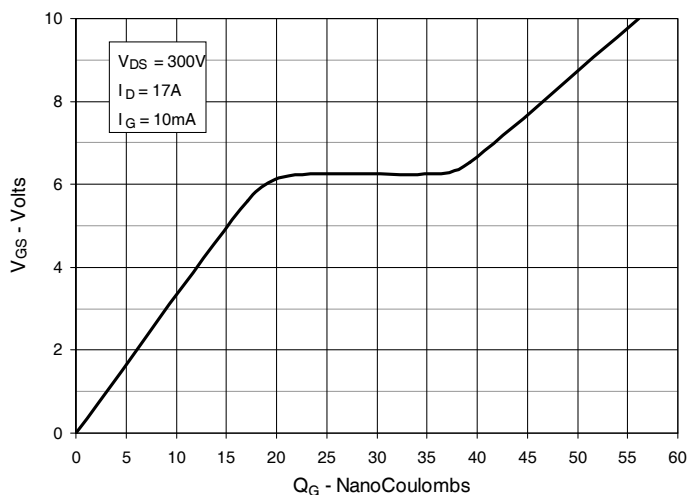
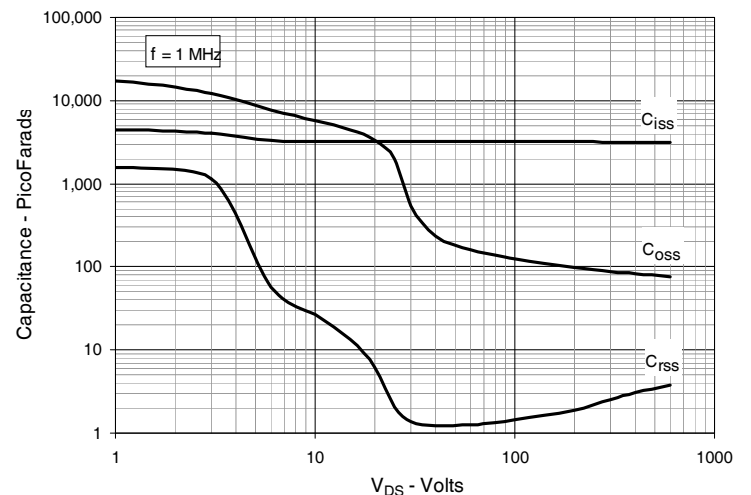


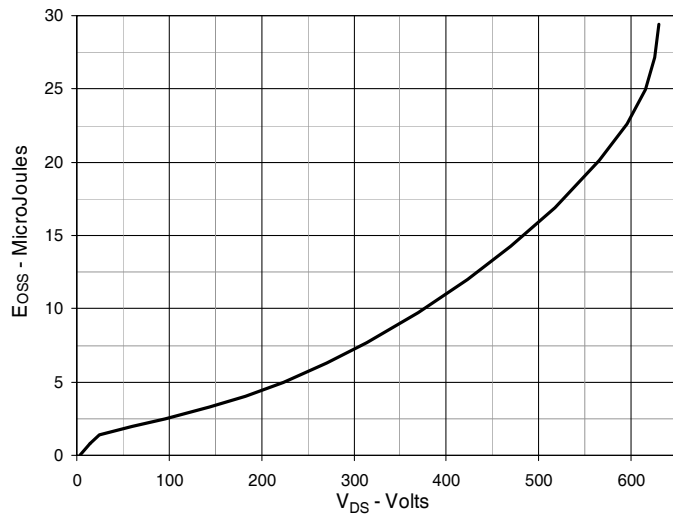
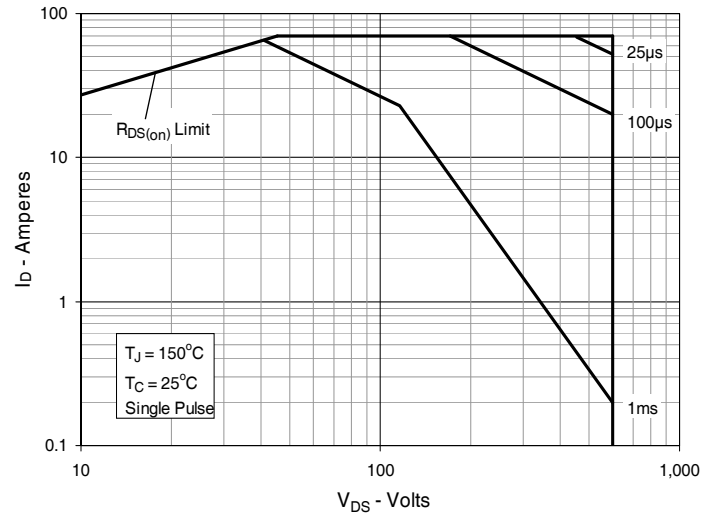
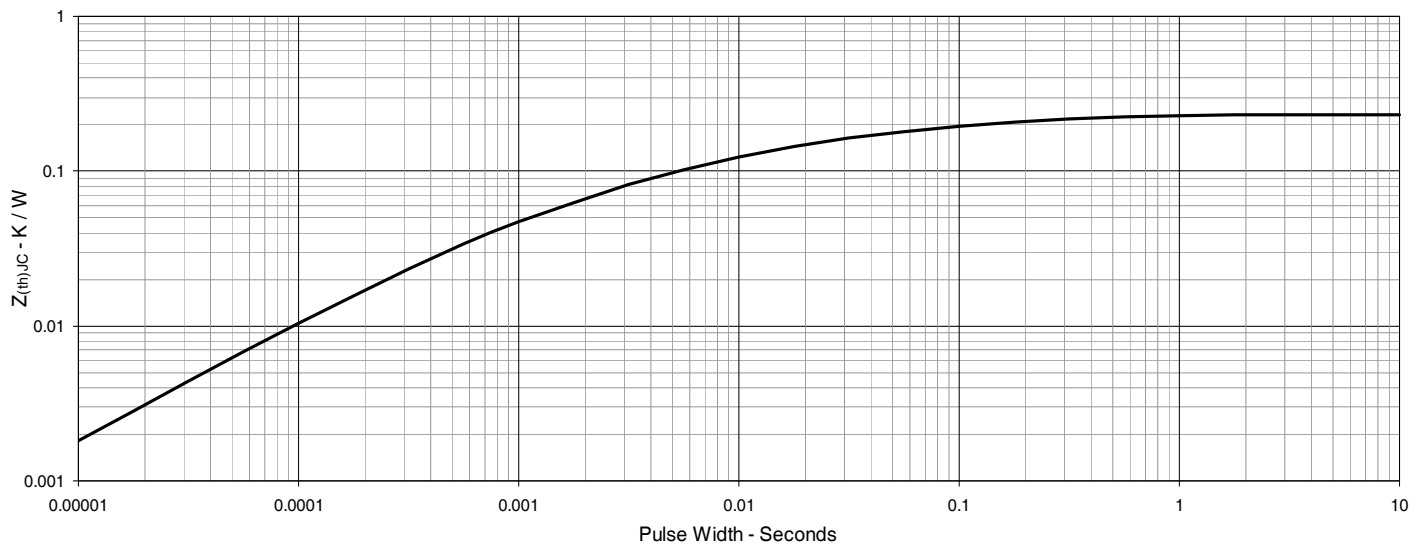
| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .190     | .205 | 4.83        | 5.21  |
| A1  | .090     | .100 | 2.29        | 2.54  |
| A2  | .075     | .085 | 1.91        | 2.16  |
| b   | .045     | .055 | 1.14        | 1.40  |
| b2  | .075     | .087 | 1.91        | 2.20  |
| b4  | .115     | .126 | 2.92        | 3.20  |
| C   | .024     | .031 | 0.61        | 0.80  |
| D   | .819     | .840 | 20.80       | 21.34 |
| D1  | .650     | .690 | 16.51       | 17.53 |
| D2  | .035     | .050 | 0.89        | 1.27  |
| E   | .620     | .635 | 15.75       | 16.13 |
| E1  | .545     | .565 | 13.84       | 14.35 |
| e   | .215 BSC |      | 5.45 BSC    |       |
| J   | --       | .010 | --          | 0.25  |
| K   | --       | .025 | --          | 0.64  |
| L   | .780     | .810 | 19.81       | 20.57 |
| L1  | .150     | .170 | 3.81        | 4.32  |
| øP  | .140     | .144 | 3.55        | 3.65  |
| øP1 | .275     | .290 | 6.99        | 7.37  |
| Q   | .220     | .244 | 5.59        | 6.20  |
| R   | .170     | .190 | 4.32        | 4.83  |
| S   | .242 BSC |      | 6.15 BSC    |       |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

|                                                                                  |           |           |           |           |             |             |             |             |             |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
|                                                                                  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
|                                                                                  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 17\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 17\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


**Fig. 7. Maximum Drain Current vs. Case Temperature**

**Fig. 8. Input Admittance**

**Fig. 9. Transconductance**

**Fig. 10. Forward Voltage Drop of Intrinsic Diode**

**Fig. 11. Gate Charge**

**Fig. 12. Capacitance**


**Fig. 13. Output Capacitance Stored Energy**

**Fig. 14. Forward-Bias Safe Operating Area**

**Fig. 15. Maximum Transient Thermal Impedance**




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